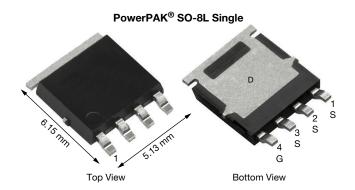
Vishay Siliconix

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET



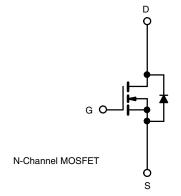
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0087			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0094			
I <sub>D</sub> (A)	58			
Configuration	Single			

#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>







ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ460AEP-T1 (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS	(T <sub>C</sub> = 25 °C, unles	s otherwise noted	1)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	60	V	
Gate-source voltage		$V_{GS}$	V <sub>GS</sub> ± 20		
Continuous drain current	T <sub>C</sub> = 25 °C	1	58		
Continuous drain current	T <sub>C</sub> = 125 °C	l <sub>D</sub>	33.4		
Continuous source current (diode conduction)		I <sub>S</sub>	62	Α	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	180		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	35		
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	61	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	68	w	
	T <sub>C</sub> = 125 °C	$P_{D}$	27		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) c, d		-	260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	68	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.2	G/VV

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = 250 μA	60	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	150	1
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.7 A	-	0.0072	0.0087	
5.		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 19.7 A, T <sub>J</sub> = 125 °C	-	-	0.0145	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10.7 A, T <sub>J</sub> = 175 °C	-	-	0.0183	Ω
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 10.3 A	-	0.0078	0.0094	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	= 15 V, I <sub>D</sub> = 10.7 A	-	88	-	S
Dynamic <sup>b</sup>						l	
Input capacitance	C <sub>iss</sub>			-	2123	2654	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 30 V, f = 1 MHz	-	282	353	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	118	148	1
Total gate charge <sup>c</sup>	Qg			-	71	106	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 18 \text{ A}$	-	9.7	-	nC
Gate-drain charge <sup>c</sup>	$Q_{\mathrm{gd}}$			-	12.5	-	
Gate resistance	$R_g$		f = 1 MHz	0.3	1.0	2.0	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	12	18	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> :	= 30 V, $R_L = 30 \Omega$	-	11	17	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A},$	$V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	=.	56	84	ns
Fall time °	t <sub>f</sub>	1		-	25	32	
Source-Drain Diode Ratings and Cha	racteristics <sup>b</sup>	<u> </u>					
Pulsed current a	I <sub>SM</sub>			-	-	180	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	7.5 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V
		1		l	l .	l	1

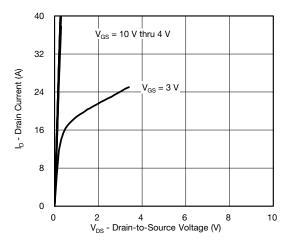
#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

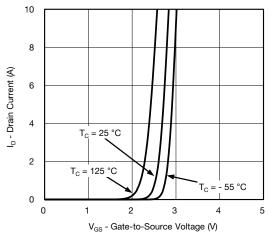
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



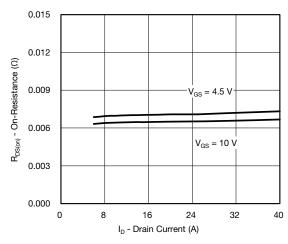
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



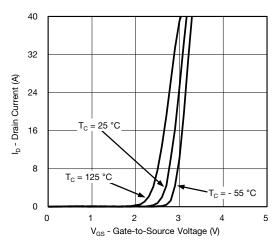
#### **Output Characteristics**



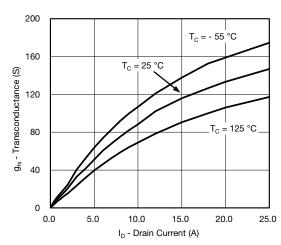
Transfer Characteristics



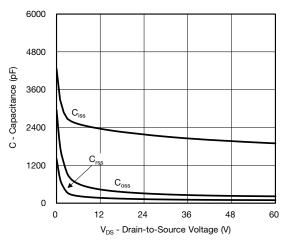
On-Resistance vs. Drain Current



**Transfer Characteristics** 



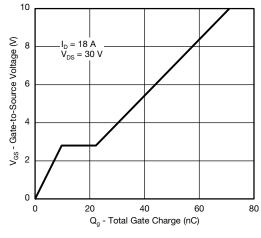
Transconductance



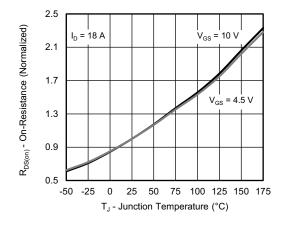
Capacitance



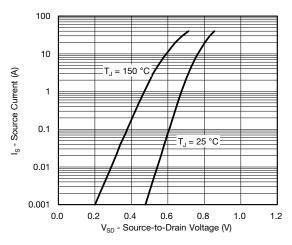
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



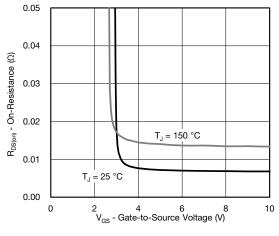
**Gate Charge** 



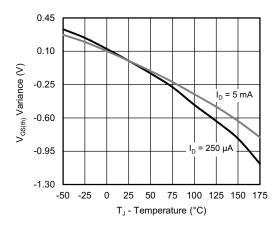
**On-Resistance vs. Junction Temperature** 



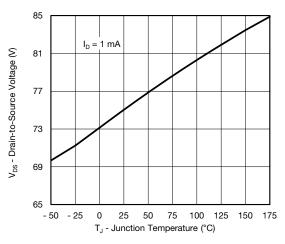
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

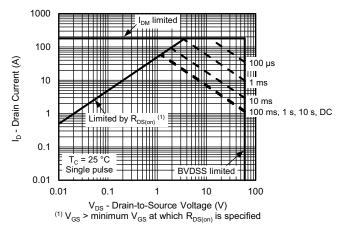


**Drain Source Breakdown vs. Junction Temperature** 

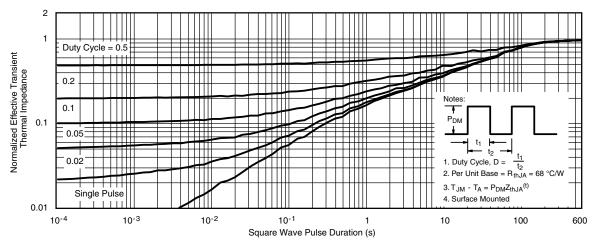
For technical questions, contact: automostechsu



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



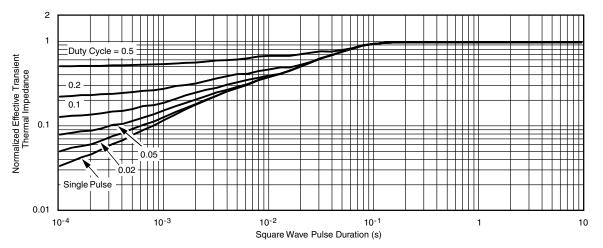
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62914">www.vishay.com/ppg?62914</a>.



# PowerPAK® SO-8L Case Outline 2



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DIM.		MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004	•	
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
Е	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W		0.23		0.009			
W1	0.41		0.016				
W2		2.82		0.111			
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

ECN: C21-1498-Rev. C, 01-Nov-2021

DWG: 6044

### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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